

In a solid state image sensor device comprising a cell area wherein unit cells each having photoelectric diodes are arranged in a matrix form on a semiconductor substrate, the cell area being composed of a photo-sensitive pixel region for sensing an image, and an optical black pixel region for defining an optical black level, and a vertical shift register for selecting the unit cells of the image sensing cell array, in a group along each of horizontal lines, and vertical signal lines, each of which reads each of signals from the unit cells selected by turning on an address register by means of the vertical shift register, the vertical signal lines in the optical black pixel region are connected with each other through a wiring. Since the vertical signal lines in the optical black pixel region are connected with each other by a wiring, even if outputs from an optical black pixel region vary in the pixels, the outputs are made averaged and uniform and a variation in fixed pattern noises between the horizontal lines are reduced.